



N-CHANNEL ENHANCEMENT MODE MOSFET WITH SCHOTTKY DIODE

Features

- DIOFET utilizes a unique patented process to monolithically integrate a MOSFET and a Schottky in a single die to deliver:
 - Low $R_{DS(ON)}\,$ minimizes conduction losses
 - Low V_{SD} reducing the losses due to body diode conduction
 - Low Q_{rr} lower Q_{rr} of the integrated Schottky reduces body diode switching losses
 - Low gate capacitance (Q_q/Q_{qs}) ratio reduces risk of shootthrough or cross conduction currents at high frequencies
 - Avalanche rugged $I_{\mbox{\scriptsize AR}}$ and $E_{\mbox{\scriptsize AR}}$ rated
- Lead Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

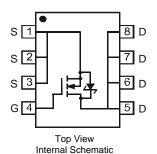
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.072 grams (approximate)





Top View



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 3) V _{GS} = 10V	Steady State	T _A = 25°C T _A = 85°C	I _D	11 6.6	А
Pulsed Drain Current (Note 4)			I _{DM}	80	Α
Avalanche Current (Notes 4 & 5)			I _{AR}	17	Α
Repetitive Avalanche Energy (Notes 4 & 5) L = 0.3mH			E _{AR}	43	mJ

Thermal Characteristics

Characteristic		Value	Unit
Power Dissipation (Note 3)	P _D	1.55	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 3)	R _{0JA}	81.3	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 Device mounted on 1in * 1in FR-4 PCB with 2oz. Copper. The value in any given application depends on the user's specific board design.
- 4. Repetitive rating, pulse width limited by junction temperature.
- 5. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep $T_J = 25^{\circ}C$

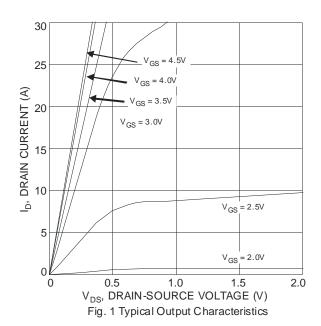


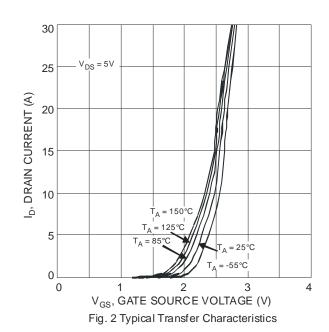
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	ı	-	0.1	mA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	Ū	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.5	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	P (-)	-	8.5 9.5	11.9 14.9	$\mathbf{m}\Omega$	$V_{GS} = 10V, I_D = 11A$	
Static Drain-Source Off-Nesistance	R _{DS} (ON)	ı				$V_{GS} = 4.5V, I_D = 8.8A$	
Forward Transfer Admittance	Y _{fs}	Ū	18	-	S	$V_{DS} = 5V, I_{D} = 10A$	
Diode Forward Voltage	V_{SD}	-	0.45	0.55	V	V _{GS} = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	ı	1276	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	į	160	-	pF		
Reverse Transfer Capacitance	C_{rss}	•	136	-	pF	1 = 1.0IVII IZ	
Gate Resistance	R_g	0.3	1.48	2.7	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_{g}	-	14.3	-	nC	$V_{DS} = 15V, V_{GS} = 4.5V, I_{D} = 8.8A$	
Total Gate Charge (V _{GS} = 10V)	Qq	-	30.6	-	nC	V _{DS} = 15V, V _{GS} = 10V, I _D = 8.8A	
Gate-Source Charge	Q _{gs}	-	3.4	-	nC		
Gate-Drain Charge	Q _{qd}	-	4.3	-	nC		
Turn-On Delay Time	t _{D(on)}	į	15.8	-	ns	$V_{GS} = 4.5V, V_{DS} = 15V,$ $R_{G} = 1.8\Omega, I_{D} = 8.8A$	
Turn-On Rise Time	t _r	ı	27.8	-	ns		
Turn-Off Delay Time	t _{D(off)}	į	29.7	-	ns		
Turn-Off Fall Time	t _f	·	13.6	-	ns		

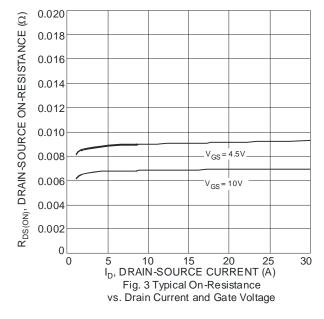
Notes:

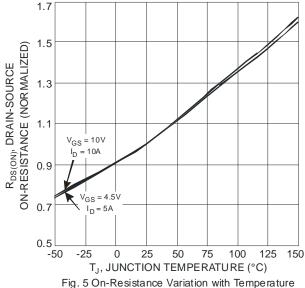
- 6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to production testing.











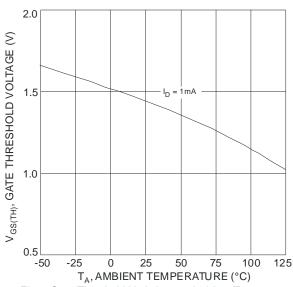
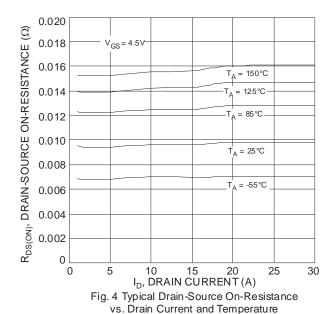
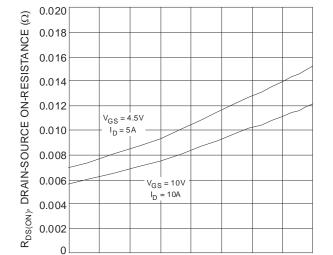


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





25

-25

-50

0

T_J, JUNCTION TEMPERATURE (°C) Fig. 6 On-Resistance Variation with Temperature

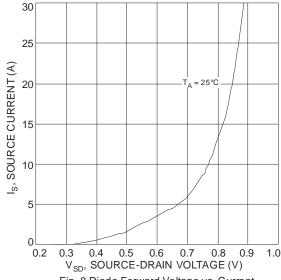
50

75

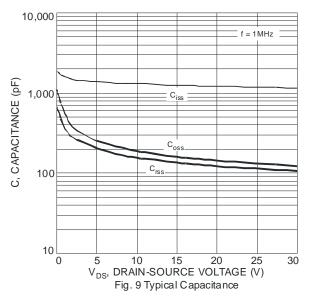
100

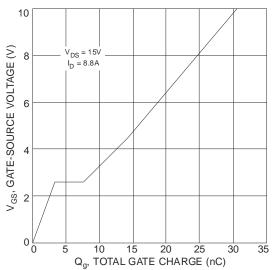
125

150

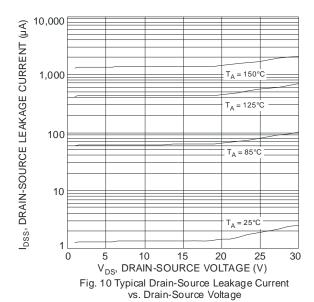












r(t), TRANSIENT THERMAL RESISTANCE D = 0.5 D = 0.1 0.9 D = 0.05 $R_{\theta JA}(t) = r(t) * R_{\theta JA}$ $R_{\theta JA} = 68^{\circ}C/W$ D = 0.02D = 0.01 D = 0.005 $T_J - T_A = P * R_{\theta JA}(t)$ Duty Cycle, D = t_1/t_2 0.001 0.0001 0.001 0.01 0.1 10 100 1,000 t₁, PULSE DURATION TIME (s) Fig. 12 Transient Thermal Response

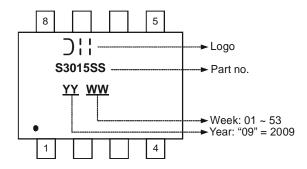


Ordering Information (Note 8)

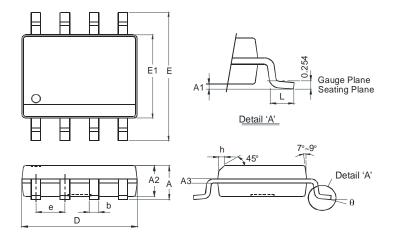
Part Number	Case	Packaging
DMS3015SSS-13	SO-8	2500 / Tape & Reel

Notes: 8. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

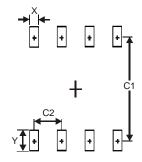


Package Outline Dimensions



SO-8					
Dim	Min	Max			
Α	ı	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	ı	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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